

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-7. (Canceled)

8. (Currently Amended) ~~The A~~ semiconductor device according to claim 2, having a plurality of diodes, and further comprising:

    a bridge-rectifier circuit comprising the diodes, and rectifying that rectifies a predetermined alternating-current voltage to a direct-current voltage and that includes:

a plurality of diodes each of which includes:

an insulating substrate;

a p-type silicon layer, the p-type silicon layer containing germanium;

an intrinsic silicon layer joined to the p-type silicon layer; and

a n-type silicon layer joined to the intrinsic silicon layer,

the p-type silicon layer, the intrinsic silicon layer and the n-type silicon layer

being disposed on the insulating substrate,

the n-type silicon layer being a ring shape,

the intrinsic silicon layer being surrounded by the n-type silicon  
layer, and

the p-type silicon layer being surrounded by the intrinsic silicon layer.

9-11. (Canceled)